BDY26CZ

NPN SILICON TRANSISTORS, DIFFUSED MESA.

They are NPN transistors mounted in Jedec TO-3.
LF Large Signal Power Amplification.
High Current Fast Switching.
Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CEO}	Collector-Emitter Voltage		220	V
V_{CBO}	Collector-Base Voltage		300	V
V_{EBO}	Emitter-Base Voltage		10	V
I_C	Collector Current		6	A
I_B	Base Current		3	A
P_{TOT}	Power Dissipation	@ T_C = 25°	87.5	W
T_J	Junction Temperature		200	°C
T_S	Storage Temperature		-65 to +200	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	2	°C/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage (*)	I_C=50 mA, I_B=0	220	-	-	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (*)	I_C=3 mA	300	-	-	V
I_{CEO}	Collector-Emitter Cutoff Current	V_{CE}=220 V	-	-	1.0	mA
I_{EBO}	Emitter-Base Cutoff Current	V_{EB}=10 V	-	-	1.0	mA
I_{CES}	Collector-Emitter Cutoff Current	V_{CE}=250 V V_{BE}=0 V	-	-	1.0	mA
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	I_C=2.0 A, I_B=0.25 A	-	-	0.6	V
$V_{BE(SAT)}$	Base-Emitter saturation Voltage (*)	I_C=2.0 A, I_B=0.25 A	-	-	1.2	V
h_{FE}	Static Forward Current transfer ratio (*)	V_{CE}=4 V, I_C=1 A	-	90	-	-
		V_{CE}=4 V, I_C=2 A	75	82	180	
		V_{CE}=0.5 V, I_C=250 mA	60	-	-	
f_T	Transition Frequency	V_{CE}=15 V, I_C=0.5 A f=10 MHz	10	-	-	MHz
$t_d + t_r$	Turn-on time	I_C=5 A I_B=1 A	-	0.3	0.5	µs
$t_s + t_f$	Turn-off time	I_C=5 A I_{B1}=1 A I_{B2}=-0.5 A	-	1.5	2.0	µs

(*) Pulse Width ≈ 300 µs, Duty Cycle ∠ 2.0%

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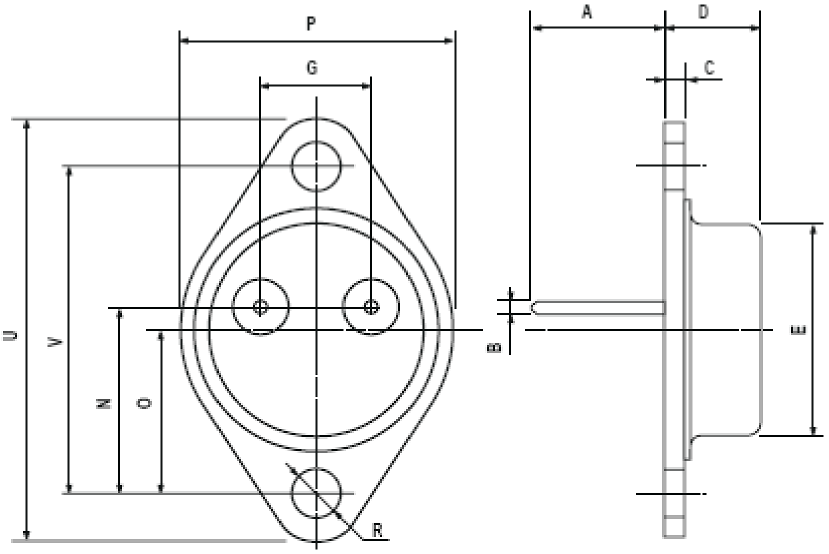
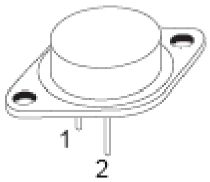
MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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